## Full Counting Statistics of Multiple Andreev Re ections

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We derive the full distribution of transm itted particles through a superconducting point contact of arbitrary transparency under voltage bias. The charge transport is dom inated by multiple Andreev re ections. The counting statistics is a multinom ial distribution of processes, in which multiple charges ne (n = 1;2;3;:::) are transferred through the contact. For zero tem perature we obtain analytical expressions for the probabilities of the multiple Andreev re ections. The current, shot noise and high current cum ulants in a variety of situations can be obtained from our result.

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The complete understanding of the electronic transport in mesoscopic systems requires information that goes beyond the analysis of the current. This explains the great attention devoted in the last years to current uctuations in these system s [1]. An important goal is to obtain the full current distribution. This was realized by Levitov and coworkers [2], who borrowed the concept of full counting statistics (FCS) for photons and adapted it to electrons in m esoscopic system s. FCS gives the probability P (N ) that N charge carriers pass through a conductor in the measuring time. From the know ledge of these probabilities one can easily derived not only the conductance and noise, but all the cum ulants of the current distribution. Since the introduction of FCS for electronic system s, the theory has been sophisticated and applied to m any di erent contexts (see a recent review, [3]). In particular one of the authors and N azarov have show n that, based on a Keldysh-G reen's function method, one can calculate in a uni ed m anner the FCS of all contacts involving superconducting elements [5].

In the context of superconductivity the basic situation, in which the FCS has not been yet investigated, is a point contact between two superconductors out of equilibrium . In this system the transport properties for voltages V below the superconducting gap are dom inated by coherent multiple Andreev re ections (MAR) [6]. In these processes a quasiparticle undergoes a cascade of Andreev re ections until it reaches an empty state in one of the leads. Recently, the microscopic theory of MAR [7] has provided a new insight into this problem and has allowed the calculation of properties beyond the current such as the shot noise [8]. The predictions of this theory have been quantitatively tested in an impressive series of experim ents in atom ic-size contacts [9, 10, 11]. In particular, the analysis of the shot noise [8, 11] has suggested, that the current at subgap energies proceeds in \giant" shots, with an e ective charge q e(1 + 2 = ieV). How ever, strictly speaking, the question of whether the charge in these contacts is indeed transferred in big chunks can only be rigorously resolved by the analysis of the FCS. This leads us to the central question addressed in this

paper: what is the FCS of MAR?

The answer, which we derive below, is that the statistics is a multinomial distribution of multiple charge transfers. Technically, we nd that the cumulant generating function (CGF) for a voltage V has the form

$$S() = \frac{t_0}{h} \int_{0}^{Z_{eV}} dE \ln 1 + P_n (E;V) e^{in} 1 :$$
(1)

The CGF is related to the FCS by P(N) =  $\binom{d}{d} = 2 \exp[S()]$  iN ]. The dimension the sum in Eq.(1) correspond to transfers of multiple charge quanta ne at energy E with the probability  $P_n$  (E;V), which can be seen by the (2 =n)-periodicity of the accompanying -dependent counting factor. This is the main result of our work and it proves, that the charges are indeed transferred in large quanta.

To arrive at these conclusions, we consider a voltagebiased superconducting point contact, i.e. two superconducting electrodes linked by a constriction, which is shorter than the coherence length and is described by a transm ission probability T. To obtain the FCS in our system of interest we make use of the Keldysh-G reen's function approach to FCS introduced N azarov and one of the authors [4, 5]. The FCS of superconducting constrictions has the general form [5]

$$S() = \frac{t_0}{h} Trln 1 + \frac{T}{4} fG_1(); G_2g 2 : (2)$$

Here  $G_{1(2)}$  denote matrix G reen's functions of the left and the right contact. The symbol in plies that the products of the G reen's functions are convolutions over the internal energy arguments, i.e.  $(G_1 \quad G_2) \in ; E^0) =$  $dE_1 \quad G_1 \in ; E_1)G_2 (E_1; E^0)$ . The trace runs not only over the K eldysh-N am bu space, but also includes integration energy. For a superconducting contact at nite bias voltage the CGF depends on time and Eq. (2) is integrated over a long measuring time  $t_0$ , much larger than the inverse of the Josepshon frequency.

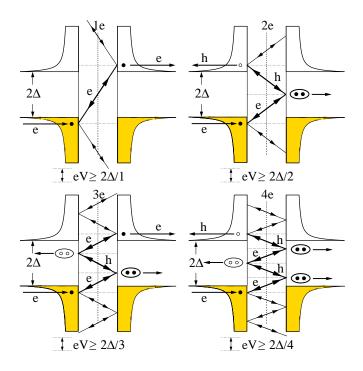


FIG.1: Schematic representation of the MARs for BCS superconductors with gap . We have sketched the density of states of both electrodes. In the upper left panel we describe the process in which a single electron tunnels through the system overcoming the gap due to a voltage eV 2. The other panels show MARs of order n = 2;3;4. In these processes an incoming electron at energy E undergoes at least n 1 Andreev re ections to nally reach an empty state at energy E + neV. In these MARs a charge ne is transferred with a probability, which for low transparencies goes as T<sup>n</sup>. At zero tem perature they have a threshold voltage eV = 2 = n. The arrows pointing to the left in the energy trajectories indicate that a quasiparticle can be norm al re ected. The lines at energies below E and above E + neV indicate that after a detour a quasiparticle can be backscattered to nally contribute to the MAR of order n.

Let us now describe the G reen's functions entering Eq. (2). The counting eld is incorporated into the matrix G reen's function of the left electrode as follows

$$G_1(;t;t^0) = e^{i_{\kappa} = 2} G_1(t;t^0) e^{i_{\kappa} = 2}$$
: (3)

Here  $G_1$  (t;t<sup>0</sup>) is the reservoir G reen's function in the absence of the counting eld and  $_K = ^3 _3 a$  matrix in K eldysh (`)-N am bu () space. We set the chemical potential of the right electrode to zero and represent the G reen's functions by  $G_1$  (t;t<sup>0</sup>) =  $e^{ieV t_3}G_S$  (t t)  $e^{ieV t^0_3}$  and  $G_2$  (t;t<sup>0</sup>) =  $G_S$  (t t). Here, we have not included the dc part of the phase, since it can be shown that it drops from the expression of the dc FCS at nite bias.  $G_S$  is the G reen's function of a superconducting reservoir (we consider the case of a symmetric junction), which reads

$$G_{S}(E) = (A R)f + R (A R)f (A R)(1 f) R A)f + A : (4)$$

Here R (A) (E) are retarded and advanced G reen's functions of the leads and f (E) is the Ferm i function. A d-vanced and retarded functions in (4) have the N am bustructure R (A) =  $g^{R,A}_{3} + f^{R,A}_{1}$  fullling the norm alization condition  $f^{2} + g^{2} = 1$ . They depend on energy and the superconducting order parameter .

In Eq. (2) the matrix appearing inside the logarithm has an in nite dimension in energy space. In the case of N-N or N-S contacts such a matrix is diagonal in this space, which makes almost trivial the evaluation of the FCS. In the S-S case at nite bias this is no longer true, which introduces an enormous complication.

We now tackle the problem of how the functional convolution in Eq. (2) can be treated. The tim e-dependence of the G reen's functions leads to a representation of the form G (E;  $E^0$ ) =  $_{n}$  G<sub>0,n</sub> (E) (E  $E^{0}$  + neV), where n = 0; 2. Restricting the fundamental energy interval to  $E = E^0 2$  [0; eV] allows to represent the convolution as matrix product, i.e. ( $G_1 = G_2$ ) (E;  $E^0$ ) !  $(G_{1}G_{2})_{n,m} (E; E^{0}) = \int_{k} (G_{1})_{n,k} (E; E^{0}) (G_{2})_{k,m} (E; E^{0}).$ W riting the CGF as S ( ) =  $(t_0=h)TrlnQ$ , where Q =  $1 + (T=2) G_1() G_2$  [12]. The trace in this new representation is written as  ${}^{R_{eV}}_{0} dE {}^{P}_{n}$  Trln Q  ${}_{nn}$ . In this way the functional convolution is reduced to matrix algebra for the in nite-dimensional matrix Q. Still, the task to compute TrlnQ is nontrivial. However, noting that Trln Q = ln det Q, it is obvious at this stage that detQ has the form of a Fourier series in , which allows us to write the CGF as follows

$$S() = \frac{t_0}{h} \int_{0}^{Z_{eV}} dE \ln P_n^0(E;V) e^{in} : (5)$$

K eeping in m ind the norm alization S (0) = 0, it is clear that one can rewrite this expression in the form anticipated in Eq. (1), where the probabilities are given by  $P_n (E; V) = P_n^0 (E; V) = \sum_{n=1}^{n=1} P_n^0 (E; V)$ . O fcourse, one has still to extract the expression of these probabilities from the determ inant of Q, which is a non-trivial task. It turns out that Q has a block-tridiagonal form, which allows to use a standard recursion technique. We de ne the following 4 4 m atrices

$$F_{n} = Q_{n;n} Q_{n;n} 2F_{n}^{1} 2Q_{n} 2;n;n 2$$
  

$$F_{0} = Q_{0;0} Q_{0;2}F_{2}^{1}Q_{2;0} Q_{0;2}F_{2}^{1}Q_{2;0};$$
(6)

where  $Q_{n,m}$  (E) = Q (E + neV; E + m eV). W ith these de nitions, det Q is simply given by det Q =  $\begin{bmatrix} 1 \\ j=1 \end{bmatrix}$  det  $F_{2j}$ . In practice, det  $F_n = 1$  if  $j_n j = j_e V j$ . This reduces the problem to the calculation of the determ inants of 4 4 m atrices.

In the zero-tem perature lim it one can work out this idea analytically to obtain the following expressions for the probabilities

$$P_{n}^{0}(\mathbf{E};\mathbf{V}) = \overset{\mathbf{X}^{1}}{K_{n+1}} \begin{pmatrix} \mathbf{u} & \mathbf{u} & \mathbf{u} & \mathbf{u} \\ \mathbf{Y}^{1} & \mathbf{u} & \mathbf{u} \\ \mathbf{U}^{2} = \mathbf{u} & \mathbf{U}^{2} = \mathbf{u} \\ \mathbf{U}^{2} = \mathbf{U}^{2} & \mathbf{U}^{2} = \mathbf{U}^{2} \\ \mathbf{U}^{2} = \mathbf{U}^{2} & \mathbf{U}^{2} \\ \mathbf{U}^{2} = \mathbf{U}^{2} \\ \mathbf{U}$$

Here, we have used the shorthand  $g_n^{A,R}$  (E)  $g_n^{A,R}$  (E + neV), and de ned

$$Z_{n} = 1 \frac{p_{\overline{T}}}{2} (g_{(n+1)} g_{n}) \frac{T}{4} (f_{(n+1)})^{2} B_{(n+2)}; n = 0;$$
(8)

where = R; A, K<sub>n,m</sub> =  $\begin{pmatrix} Q \\ j=1 \end{pmatrix} \det F_{n-2j} \begin{pmatrix} Q \\ j=1 \end{pmatrix} \det F_{m+2j}$  and the di event functions can be expressed as follows

$$B_{n}^{1} = 1 \frac{p_{\overline{T}}}{2} (g_{n} g_{(n-1)}) \frac{T}{4} (f_{n})^{2} = Z_{n}; \det F_{n} = \frac{Y}{Z_{n}} (1 \frac{p_{\overline{T}}}{2} (g_{n} g_{(n-1)})) \frac{T}{4} (f_{n})^{2}$$
$$J_{n} = \frac{p_{\overline{T}}}{2} (g_{n}^{A} g_{n}^{A}) Z_{n}^{A} Z_{n}^{A} \frac{T}{4} (f_{n}^{A} f_{n}^{A}) \frac{T}{4} (f_{n}^{A} f_{n}^{A}) f_{n}^{A} Z_{n}^{A} + f_{n}^{A} Z_{n}^{A}$$
(9)

Notice that, since at zero tem perature the charge only ows in one direction, only the  $P_n$  with n 0 survive. It is worth stressing that the full inform ation about the transport properties of superconducting point contacts is encoded in these probabilities. Let us remark that  $P_n \times V$  are positive numbers bounded between 0 and 1. Although at a rst glance they look com plicated, they can be easily computed and provide the most e cient way to calculate the transport properties of these contacts. In practice, to determ ine the functions  $B_n^{A,R}$  and det  $F_n$ , one can use the boundary condition  $B_n^{\tilde{A};R} = \det F_n = 1 \text{ for jnj}$ =jeV j. For perfect transparency (T = 1) the previous expressions greatly sim plify and the probabilities  ${\tt P}_n \times {\tt V}$  ) can be written as

where a(E) is the Andreev rejection coecient defined as  $a(E) = if^{R}(E) = 1 + g^{R}(E)$ , and  $a_{n} = a(E + neV)$ .

In view of Eqs. (7-9) the probabilities  $P_n$  can be interpreted in the following way.  $P_n$  is the probability of a MAR of order n, where a quasiparticle in an occupied state at energy E is transmitted to an empty state at energy E + neV. The typical structure of the leading contribution to this probability consists of the product of three terms. First,  $J_0$  gives the probability to inject the incoming quasiparticle at energy E. The term  $\sum_{k=1}^{n-1} (T=4) f_k^A f$  describes the cascade of n 1 A ndreev re ections, in which an electron is re ected as a hole and vice versa, gaining an energy eV in each re ection. Finally,  $J_n$  gives the probability to inject a quasiparticle in

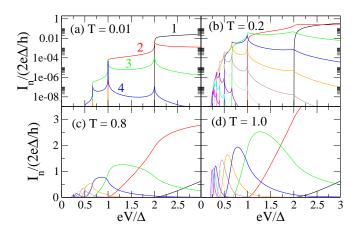


FIG.2: Current contribution of processes n = 1; ...; 10, from right to left, as a function of voltage for BCS superconductors of gap . The di erent panels correspond to di erent transmissions. Notice the logarithm ic scale in the upper panels.

an empty state at energy E to neV. In the tunnel regime P<sub>n</sub> (E;V) = (T<sup>n</sup>=4<sup>n</sup> <sup>1</sup>) <sub>0 n</sub>  $\sum_{k=1}^{n-1} j \xi_k^A j$ , (E) being the reservoir density of states. This interpretation is illustrated in Fig. 1, where we show the rst four processes for BCS superconductors. The product of the determ inants in the expression of P<sub>n</sub><sup>0</sup> (see Eq. (7)) describes the possibility that a quasiparticle be rejected and make an excursion to energies below E or above E + neV [13]. In the tunnel regime this possibility is very unlikely and at perfect transparency is forbidden. As can be seen in Eq. (10), for T = 1 the quasiparticle can only move upwards in energy due to the absence of normal rejection.

From the know ledge of the FCS one can get a deep

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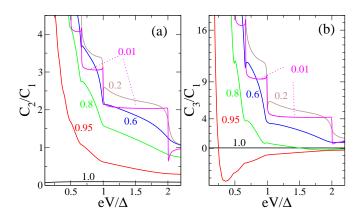


FIG. 3: Second and third cum ulant at zero tem perature for a contact between BCS superconductors. Both are norm alized to the rst cum ulant (the average current). The transm issions are indicated in the plots.

insight into the di erent transport properties by analyzing the role played by every process. For instance, in Fig. 2 we show the contribution to the<sub>R</sub>dc current of the individual processes, i.e.  $I_n = (2e=h) dE nP_n$ , for the case of BCS superconductors of gap  $\$  . In this case  $f^{A;R} = i = \langle E \rangle$ i)  $^{2}$ , where = 0<sup>+</sup>, and g<sup>A</sup>;<sup>R</sup> follows from normalization. As can be seen in Fig. 2, a MAR of order n has a threshold voltage eV =  $2 = n_{1}$ below which it cannot occur. The opening of MARs at these threshold voltages is the origin of the pronounced subgap structure visible in the di erent transport properties (see Fig. 3). Notice also that at low transmission the MAR of ordern dom inates the transport for voltages [2 = n; 2 = (n)1)], while at high transparencies several MARs give a signi cant contribution at a given voltage. This naturally explains why the elective charge is only quantized in the tunnel regime [8, 11].

From the CGF one can easily calculate the cumulants of the distribution and in turn m any transport properties. Of special interest are the rst three cumulants  $C_1 = \overline{N}$ ,  $C_2 = (\overline{N} - \overline{N})^2$  and  $C_3 = (\overline{N} - \overline{N})^3$ , which correspond to the average, width and skewness of the distribution, respectively. From the fact that the FCS is a multinom ial distribution, it follows that at zero temperature these cumulants can be expressed in term of the probabilities  $P_n$  (E;V) as  $C_n$  (V) =  $\binom{N}{0}$  dE  $C_n$  (E;V), where

$$C_{1}(E;V) = \begin{cases} X^{1} \\ nP_{n}; C_{2}(E;V) \\ n=1 \end{cases} = \begin{cases} X^{1} \\ n^{2}P_{n} \\ n=1 \end{cases} = \begin{cases} X^{1} \\ n=1 \\ C_{1}(E;V) \\ C_{1}(E;V) \\ C_{1}(E;V) \\ C_{1}(E;V) \\ n=1 \end{cases} = \begin{cases} X^{1} \\ n^{2}P_{n} \\ n^{2}P_{n} \\ C_{1}(E;V) \\ C_{$$

The rst two cumulants are simply related to the dc current,  $I = (2e=h)C_1$ , and to the zero-frequency noise  $S_I = (4e^2=h)C_2$ . In Fig. 3 we show  $C_2$  norm alized by  $C_1$ , which reproduces the results for the shot noise re-

ported in the literature [8]. In this gure we also show  $C_3$ . This cum ulant determ ines the shape of the distribution, and it is attracting considerable attention [14, 15] because it contains information on nonequilibrium physics even at tem peratures larger than the voltage. As seen in Fig. 3, at low transmissions  $C_3 = q^2 C_1$ , where q(V) =1 + Int(2 = eV) is the charge transferred in the MAR which dom inates the transport at a given voltage. This relation is a striking example of the general relation conjectured in Ref. [14], and it is simply due to the fact that the multinom ial distribution becomes Poissonian in this limit. For higher transmissions this cumulant is negative at high voltage as in the norm al state, where 2T), but it becom es positive at low  $C_3 = T (1)$ T)(1 bias. This sign change is due to the reduction of the MAR probabilities at low voltage. A fter the sign change there is a huge increase of the ratio  $C_3 = C_1$ , which is a signature of the charge transfer in large quanta. Finally, at T = 1 the cum ulants (C n with n > 1) do not com pletely vanish due to the fact that at a given voltage di erent MARs give a signi cant contribution, and therefore their probability is smaller than one (see Fig. 2(d)).

In sum m ary, we have demonstrated that in superconducting contacts at nite voltage the charge transport is described by a multinom ial distribution of multiple charge transfers. This proves that in the MAR processes the charge is indeed transmitted in large quanta. We have obtained analytically the MAR probabilities at zero tem perature, from which all the transport properties are easily computed. Our result constitutes the culm ination of the recent progress in the understanding of MARs, which are a key concept in mesoscopic superconductivity.

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same contribution and we concentrate in the analysis of the  $\,$  rst one, and we drop the subindex + .

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